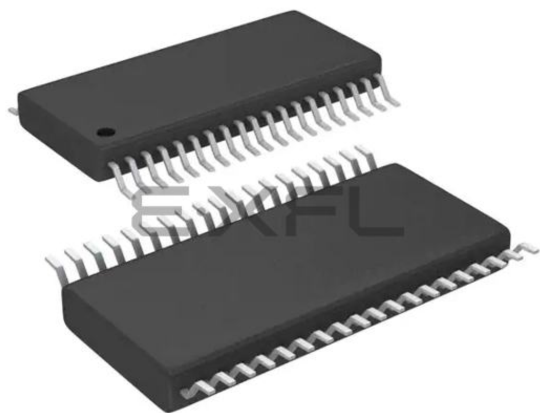

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, I²S, POR, PWM, WDT
Number of I/O	26
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	38-TFSOP (0.173", 4.40mm Width)
Supplier Device Package	PG-TSSOP-38-9
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xmc1100t038x0064abxuma1

XMC1100 Data Sheet

Revision History: V1.7 2016-08

Previous Version: V1.6	
Page	Subjects
many	Added XMC™ trademark
Page 23	Removed ADC channels from Port I/O Functions table, which are not available in XMC1100 (G1CH0, G1CH2, G1CH3, G1CH4).
Page 36	Removed auxiliary V_{REFGND} for G1CH0, as this channel is not available in XMC1100.
Page 36	Adjusted ADC sample time and sample rate to configurable limits.
Page 46	Flash Memory Parameters Table: • Erase time per page parameter is renamed to Erase time per page / sector. • Erase cycles parameter is renamed to include test condition of sum of page and sector erase cycles. • Added parameter for fixed wait states configuration.

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About this Document

This Data Sheet is addressed to embedded hardware and software developers. It provides the reader with detailed descriptions about the ordering designations, available features, electrical and physical characteristics of the XMC1100 series devices.

The document describes the characteristics of a superset of the XMC1100 series devices. For simplicity, the various device types are referred to by the collective term XMC1100 throughout this document.

XMC™1000 Family User Documentation

The set of user documentation includes:

- **Reference Manual**
  - decribes the functionality of the superset of devices.
- **Data Sheets**
  - list the complete ordering designations, available features and electrical characteristics of derivative devices.
- **Errata Sheets**
  - list deviations from the specifications given in the related Reference Manual or Data Sheets. Errata Sheets are provided for the superset of devices.

Attention: Please consult all parts of the documentation set to attain consolidated knowledge about your device.

Application related guidance is provided by **Users Guides** and **Application Notes**.

Please refer to **http://www.infineon.com/xmc1000** to get access to the latest versions of those documents.

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  - Q: VQFN
- <PPP> package pin count
- <T> the temperature range:
  - F: -40°C to 85°C
  - X: -40°C to 105°C
- <FFFF> the Flash memory size.

For ordering codes for the XMC1100 please contact your sales representative or local distributor.

This document describes several derivatives of the XMC1100 series, some descriptions may not apply to a specific product. Please see **Table 1**.

For simplicity the term **XMC1100** is used for all derivatives throughout this document.

1.2 Device Types

These device types are available and can be ordered through Infineon's direct and/or distribution channels.

Table 1 Synopsis of XMC1100 Device Types

Derivative	Package	Flash Kbytes	SRAM Kbytes
XMC1100-T016F0008	PG-TSSOP-16-8	8	16
XMC1100-T016F0016	PG-TSSOP-16-8	16	16
XMC1100-T016F0032	PG-TSSOP-16-8	32	16
XMC1100-T016F0064	PG-TSSOP-16-8	64	16
XMC1100-T016X0016	PG-TSSOP-16-8	16	16
XMC1100-T016X0032	PG-TSSOP-16-8	32	16
XMC1100-T016X0064	PG-TSSOP-16-8	64	16
XMC1100-T038F0016	PG-TSSOP-38-9	16	16
XMC1100-T038F0032	PG-TSSOP-38-9	32	16
XMC1100-T038F0064	PG-TSSOP-38-9	64	16
XMC1100-T038X0064	PG-TSSOP-38-9	64	16
XMC1100-Q024F0008	PG-VQFN-24-19	8	16
XMC1100-Q024F0016	PG-VQFN-24-19	16	16
XMC1100-Q024F0032	PG-VQFN-24-19	32	16
XMC1100-Q024F0064	PG-VQFN-24-19	64	16
XMC1100-Q040F0016	PG-VQFN-40-13	16	16

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Table 4 XMC1100 Chip Identification Number (cont'd)

Derivative	Value	Marking
XMC1100-Q040F0032	00011042 01CF00FF 00001F37 00000000 00000C00 00001000 00009000 $201ED083_H$	AB
XMC1100-Q040F0064	00011042 01CF00FF 00001F37 00000000 00000C00 00001000 00011000 $201ED083_H$	AB

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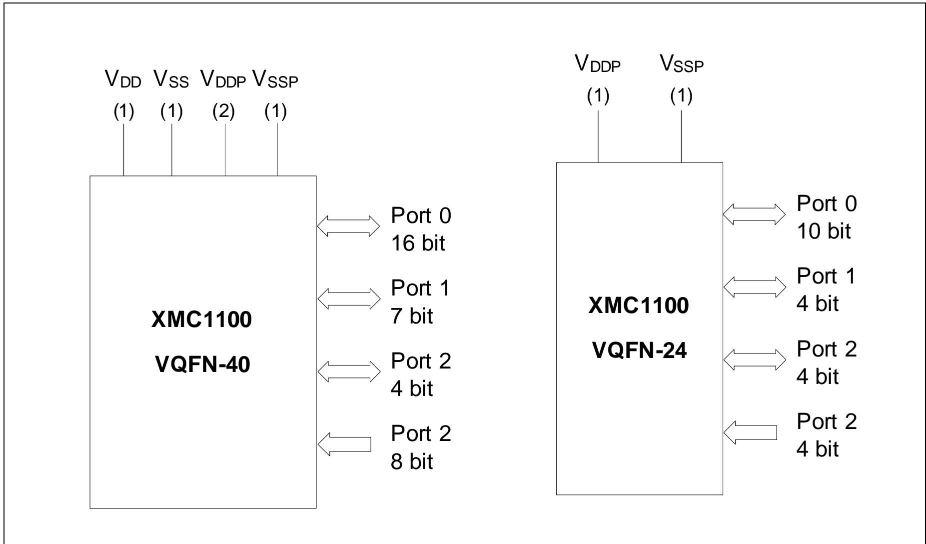

Figure 3 XMC1100 Logic Symbol for VQFN-24 and VQFN-40

2.2 Pin Configuration and Definition

The following figures summarize all pins, showing their locations on the different packages.

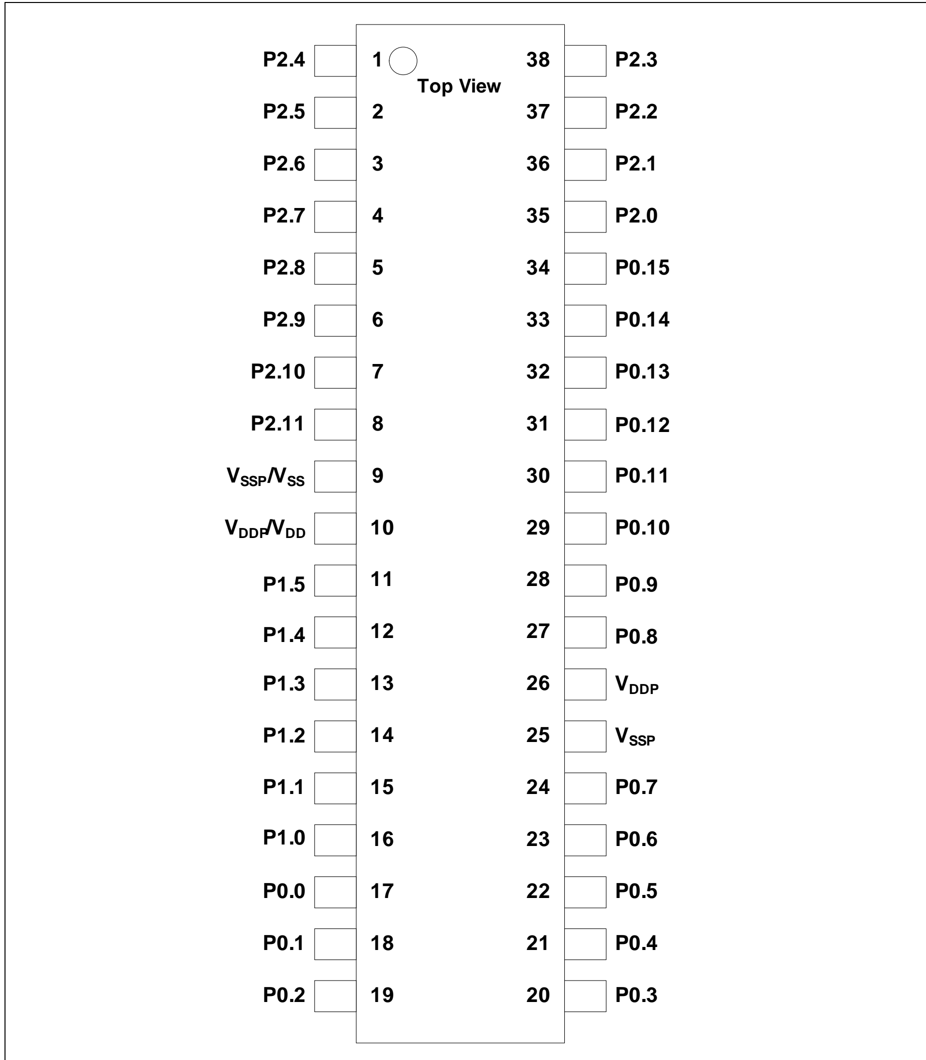

Figure 4 XMC1100 PG-TSSOP-38 Pin Configuration (top view)

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2.2.1 Package Pin Summary

The following general building block is used to describe each pin:

Table 5 Package Pin Mapping Description

Function	Package A	Package B	...	Pad Type
Px.y	N	N		Pad Class

The table is sorted by the “Function” column, starting with the regular Port pins (Px.y), followed by the supply pins.

The following columns, titled with the supported package variants, lists the package pin number to which the respective function is mapped in that package.

The “Pad Type” indicates the employed pad type:

- STD_INOUT (standard bi-directional pads)
- STD_INOUT/AN (standard bi-directional pads with analog input)
- High Current (high current bi-directional pads)
- STD_IN/AN (standard input pads with analog input)
- Power (power supply)

Details about the pad properties are defined in the Electrical Parameters.

Table 6 Package Pin Mapping

Function	VQFN 40	TSSOP 38	VQFN 24	TSSOP 16	Pad Type	Notes
P0.0	23	17	15	7	STD_INOUT	
P0.1	24	18	-	-	STD_INOUT	
P0.2	25	19	-	-	STD_INOUT	
P0.3	26	20	-	-	STD_INOUT	
P0.4	27	21	-	-	STD_INOUT	
P0.5	28	22	16	8	STD_INOUT	
P0.6	29	23	17	9	STD_INOUT	
P0.7	30	24	18	10	STD_INOUT	
P0.8	33	27	19	11	STD_INOUT	
P0.9	34	28	20	12	STD_INOUT	
P0.10	35	29	-	-	STD_INOUT	
P0.11	36	30	-	-	STD_INOUT	
P0.12	37	31	21	-	STD_INOUT	

If a pin current is outside of the **Operating Conditions** but within the overload conditions, then the parameters of this pin as stated in the Operating Conditions can no longer be guaranteed. Operation is still possible in most cases but with relaxed parameters.

Note: An overload condition on one or more pins does not require a reset.

Note: A series resistor at the pin to limit the current to the maximum permitted overload current is sufficient to handle failure situations like short to battery.

Table 12 Overload Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input current on any port pin during overload condition	I_{OV} SR	-5	–	5	mA	
Absolute sum of all input circuit currents during overload condition	I_{OVS} SR	–	–	25	mA	

Figure 9 shows the path of the input currents during overload via the ESD protection structures. The diodes against V_{DDP} and ground are a simplified representation of these ESD protection structures.

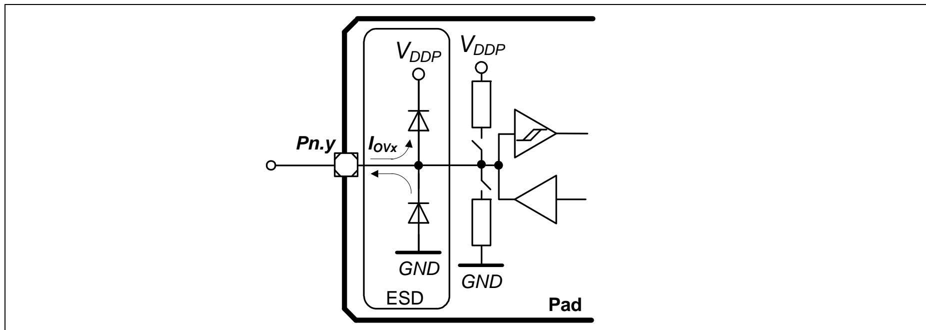

Figure 9 Input Overload Current via ESD structures

Table 13 and **Table 14** list input voltages that can be reached under overload conditions. Note that the absolute maximum input voltages as defined in the **Absolute Maximum Ratings** must not be exceeded during overload.

Table 13 PN-Junction Characterisitics for positive Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{DDP} + 0.5$ V	$V_{IN} = V_{DDP} + 0.5$ V

Table 14 PN-Junction Characterisitics for negative Overload

Pad Type	I_{OV} = 5 mA, T_J = -40 °C	I_{OV} = 5 mA, T_J = 115 °C
Standard, High-current, AN/DIG_IN	$V_{IN} = V_{SS} - 0.5$ V	$V_{IN} = V_{SS} - 0.5$ V

3.1.4 Operating Conditions

The following operating conditions must not be exceeded in order to ensure correct operation and reliability of the XMC1100. All parameters specified in the following tables refer to these operating conditions, unless noted otherwise.

Table 15 Operating Conditions Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Ambient Temperature	T_A SR	-40	–	85	°C	Temp. Range F
		-40	–	105	°C	Temp. Range X
Digital supply voltage[1]	V_{DDP} SR	1.8	–	5.5	V	
MCLK Frequency	f_{MCLK} CC	–	–	33.2	MHz	CPU clock
PCLK Frequency	f_{PCLK} CC	–	–	66.4	MHz	Peripherals clock
Short circuit current of digital outputs	I_{SC} SR	-5	–	5	mA	
Absolute sum of short circuit currents of the device	ΣI_{SC_D} SR	–	–	25	mA	

1) See also the Supply Monitoring thresholds, **Chapter 3.3.2**.

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Table 16 Input/Output Characteristics (Operating Conditions apply) (cont'd)

Parameter	Symbol		Limit Values		Unit	Test Conditions
			Min.	Max.		
Input low voltage on port pins (Large Hysteresis)	V_{ILPL}	SR	–	$0.08 \times V_{DDP}$	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Input high voltage on port pins (Large Hysteresis)	V_{IHPL}	SR	$0.85 \times V_{DDP}$	–	V	CMOS Mode (5 V, 3.3 V & 2.2 V)[10]
Rise time on High Current Pad[1]	t_{HCPR}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Fall time on High Current Pad[1]	t_{HCPF}	CC	–	9	ns	50 pF @ 5 V[2]
			–	12	ns	50 pF @ 3.3 V[3]
			–	25	ns	50 pF @ 1.8 V[4]
Rise time on Standard Pad[1]	t_R	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Fall time on Standard Pad[1]	t_F	CC	–	12	ns	50 pF @ 5 V[5]
			–	15	ns	50 pF @ 3.3 V[6]
			–	31	ns	50 pF @ 1.8 V[7]
Input Hysteresis[8]	HYS	CC	$0.08 \times V_{DDP}$	–	V	CMOS Mode (5 V), Standard Hysteresis
			$0.03 \times V_{DDP}$	–	V	CMOS Mode (3.3 V), Standard Hysteresis
			$0.02 \times V_{DDP}$	–	V	CMOS Mode (2.2 V), Standard Hysteresis
			$0.5 \times V_{DDP}$	$0.75 \times V_{DDP}$	V	CMOS Mode(5 V), Large Hysteresis
			$0.4 \times V_{DDP}$	$0.75 \times V_{DDP}$	V	CMOS Mode(3.3 V), Large Hysteresis
			$0.2 \times V_{DDP}$	$0.65 \times V_{DDP}$	V	CMOS Mode(2.2 V), Large Hysteresis

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Table 17 ADC Characteristics (Operating Conditions apply)[1] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum sample rate in 8-bit mode [3]	f_{C8} CC	–	–	f_{ADC} / 38.5	–	1 sample pending
		–	–	f_{ADC} / 54.5	–	2 samples pending
RMS noise [4]	EN_{RMS} CC	–	1.5	–	LSB 12	DC input, V_{DD} = 5.0 V, V_{AIN} = 2.5 V, 25°C
DNL error	EA_{DNL} CC	–	±2.0	–	LSB 12	
INL error	EA_{INL} CC	–	±4.0	–	LSB 12	
Gain error with external reference	EA_{GAIN} CC	–	±0.5	–	%	SHSCFG.AREF = 00_B (calibrated)
Gain error with internal reference [5]	EA_{GAIN} CC	–	±3.6	–	%	SHSCFG.AREF = $1X_B$ (calibrated), -40°C - 105°C
		–	±2.0	–	%	SHSCFG.AREF = $1X_B$ (calibrated), 0°C - 85°C
Offset error	EA_{OFF} CC	–	±8.0	–	mV	Calibrated, V_{DD} = 5.0 V

1) The parameters are defined for ADC clock frequency f_{SH} = 32MHz.

2) No pending samples assumed, excluding sampling time and calibration.

3) Includes synchronization and calibration (average of gain and offset calibration).

4) This parameter can also be defined as an SNR value: SNR[dB] = 20 × log(A_{MAXeff} / N_{RMS}).
With $A_{MAXeff} = 2^N / 2$, SNR[dB] = 20 × log (2048 / N_{RMS}) [N = 12].
N_{RMS} = 1.5 LSB12, therefore, equals SNR = 20 × log (2048 / 1.5) = 62.7 dB.

5) Includes error from the reference voltage.

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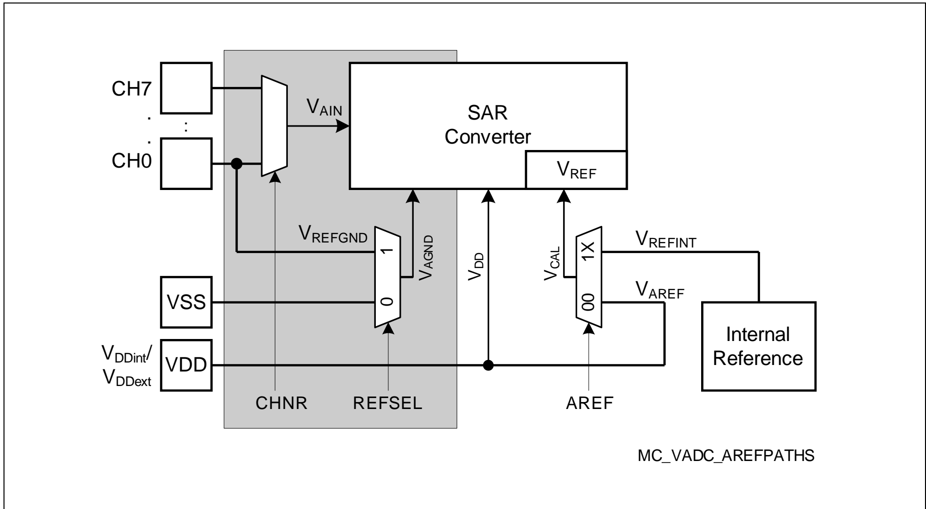

Figure 10 ADC Voltage Supply

Figure 11 shows typical graphs for active mode supply current for V_{DDP} = 5V, V_{DDP} = 3.3V, V_{DDP} = 1.8V across different clock frequencies.

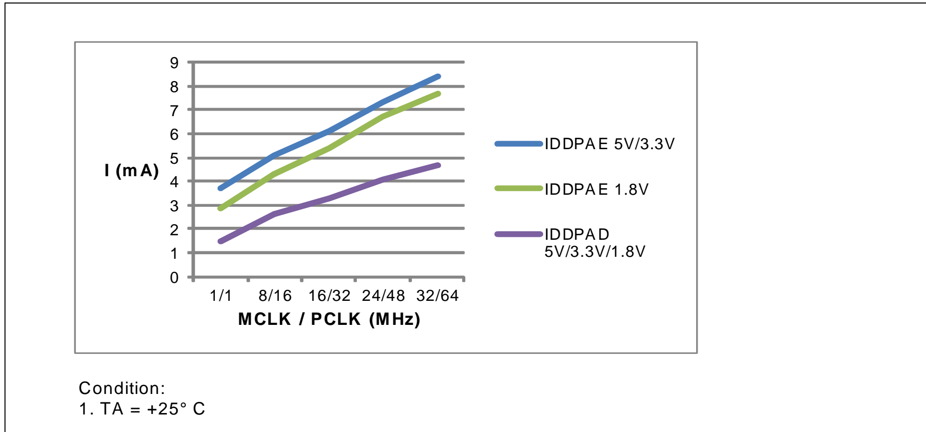

Figure 11 Active mode, a) peripherals clocks enabled, b) peripherals clocks disabled: Supply current I_{DDPA} over supply voltage V_{DDP} for different clock frequencies

Figure 12 shows typical graphs for sleep mode current for V_{DDP} = 5V, V_{DDP} = 3.3V, V_{DDP} = 1.8V across different clock frequencies.

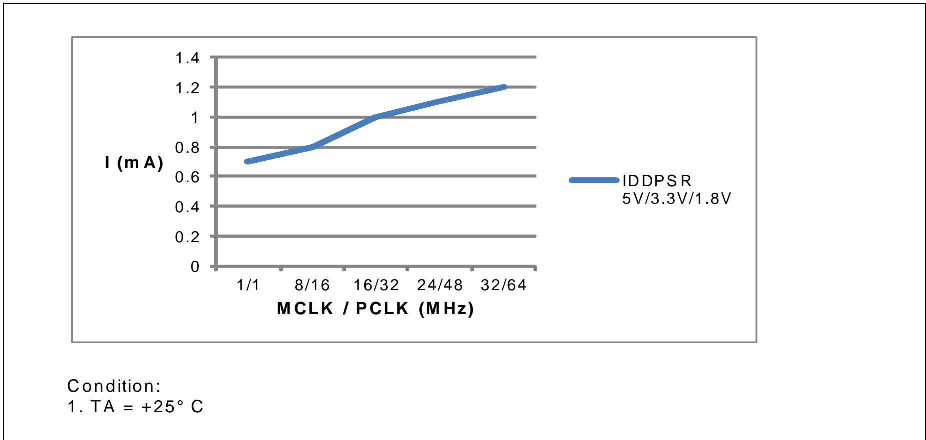

Figure 12 Sleep mode, peripherals clocks disabled, Flash powered down: Supply current I_{DDPSR} over supply voltage V_{DDP} for different clock frequencies

Table 22 Power-Up and Supply Monitoring Parameters (Operating Conditions apply)[1] (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
V_{DDP} brownout reset voltage	V_{DDPBO} CC	1.55	1.62	1.75	V	calibrated, before user code starts running
V_{DDP} voltage to ensure defined pad states	V_{DDPPA} CC	–	1.0	–	V	
Start-up time from power-on reset	t_{SSW} SR	–	320	–	µs	Time to the first user code instruction in all start-up modes[4]
BMI program time	t_{BMI} SR	–	8.25	–	ms	Time taken from a user-triggered system reset after BMI installation is is requested

1) Not all parameters are 100% tested, but are verified by design/characterisation.

2) A capacitor of at least 100 nF has to be added between V_{DDP} and V_{SSP} to fulfill the requirement as stated for this parameter.

3) Valid for a 100 nF buffer capacitor connected to supply pin where current from capacitor is forwarded only to the chip. A larger capacitor value has to be chosen if the power source sink a current.

4) This values does not include the ramp-up time. During startup firmware execution, MCLK is running at 32 MHz and the clocks to peripheral as specified in register CGATSTAT0 are gated.

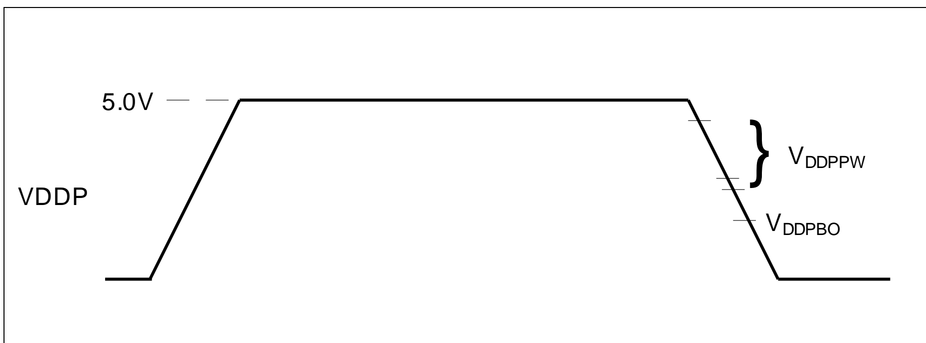

Figure 16 Supply Threshold Parameters

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Figure 17 shows the typical curves for the accuracy of DCO1, with and without calibration based on temperature sensor, respectively.

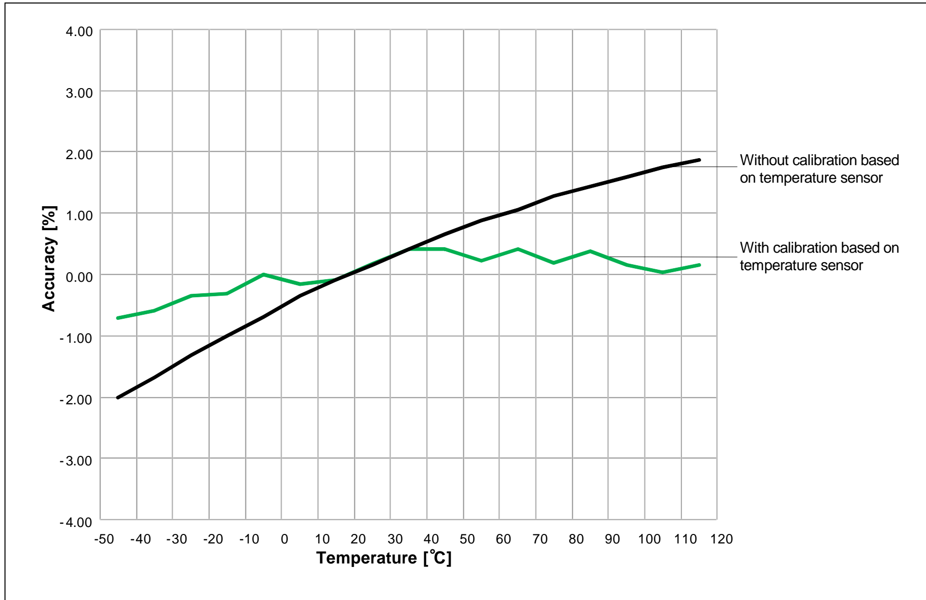

Figure 17 Typical DCO1 accuracy over temperature

Table 24 provides the characteristics of the 32 kHz clock output from digital controlled oscillators, DCO2 in XMC1100.

Table 24 32 kHz DCO2 Characteristics (Operating Conditions apply)

Parameter	Symbol		Limit Values			Unit	Test Conditions
			Min.	Typ.	Max.		
Nominal frequency	f_{NOM}	CC	–	32.75	–	kHz	under nominal conditions[1] after trimming
Accuracy	Δf_{LT}	CC	-1.7	–	3.4	%	with respect to f_{NOM}(typ), over temperature (0 °C to 85 °C)
			-3.9	–	4.0	%	with respect to f_{NOM}(typ), over temperature (-40 °C to 105 °C)

1) The deviation is relative to the factory trimmed frequency at nominal V_{DDC} and T_A = + 25 °C.

4 Package and Reliability

The XMC1100 is a member of the XMC™1000 Family of microcontrollers. It is also compatible to a certain extent with members of similar families or subfamilies.

Each package is optimized for the device it houses. Therefore, there may be slight differences between packages of the same pin-count but for different device types. In particular, the size of the exposed die pad may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

4.1 Package Parameters

Table 33 provides the thermal characteristics of the packages used in XMC1100.

Table 33 Thermal Characteristics of the Packages

Parameter	Symbol	Limit Values		Unit	Package Types
		Min.	Max.		
Exposed Die Pad Dimensions	Ex × Ey CC	-	2.7 × 2.7	mm	PG-VQFN-24-19
		-	3.7 × 3.7	mm	PG-VQFN-40-13
Thermal resistance Junction-Ambient	$R_{\Theta JA}$ CC	-	104.6	K/W	PG-TSSOP-16-8[1)]
		-	70.3	K/W	PG-TSSOP-38-9[1)]
		-	46.0	K/W	PG-VQFN-24-19[1)]
		-	38.4	K/W	PG-VQFN-40-13[1)]

1) Device mounted on a 4-layer JEDEC board (JESD 51-5); exposed pad soldered.

Note: For electrical reasons, it is required to connect the exposed pad to the board ground V_{SSP}, independent of EMC and thermal requirements.

4.1.1 Thermal Considerations

When operating the XMC1100 in a system, the total heat generated in the chip must be dissipated to the ambient environment to prevent overheating and the resulting thermal damage.

The maximum heat that can be dissipated depends on the package and its integration into the target board. The “Thermal resistance $R_{\Theta JA}$” quantifies these parameters. The power dissipation must be limited so that the average junction temperature does not exceed 115 °C.

The difference between junction temperature and ambient temperature is determined by
$\Delta T = (P_{INT} + P_{IOSTAT} + P_{IODYN}) \times R_{\Theta JA}$

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The internal power consumption is defined as
$P_{INT} = V_{DDP} \times I_{DDP}$ (switching current and leakage current).

The static external power consumption caused by the output drivers is defined as
$P_{IOSTAT} = \Sigma((V_{DDP}-V_{OH}) \times I_{OH}) + \Sigma(V_{OL} \times I_{OL})$

The dynamic external power consumption caused by the output drivers (P_{IODYN}) depends on the capacitive load connected to the respective pins and their switching frequencies.

If the total power dissipation for a given system configuration exceeds the defined limit, countermeasures must be taken to ensure proper system operation:

- Reduce V_{DDP}, if possible in the system
- Reduce the system frequency
- Reduce the number of output pins
- Reduce the load on active output drivers

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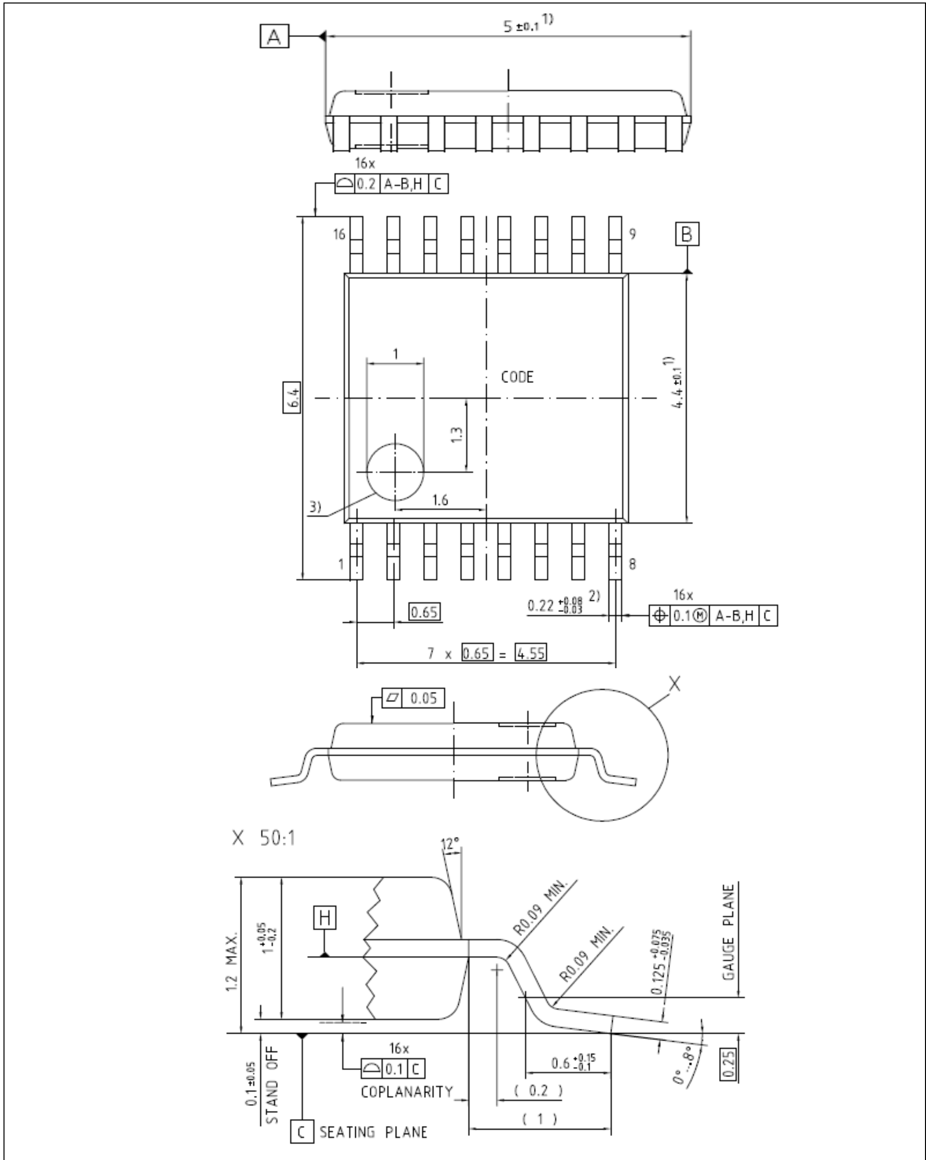

Figure 24 PG-TSSOP-16-8